


# BCR08AS-8

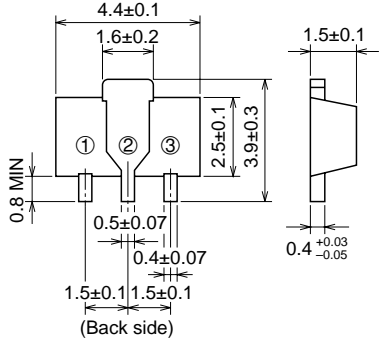
LOW POWER USE  
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

**BCR08AS-8**

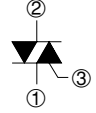


- **IT (RMS)** ..... **0.8A**
- **VDRM** ..... **400V**
- **IFGT I , IRGT I , IRGT III** ..... **5mA**
- **IFGT III** ..... **10mA**

**OUTLINE DRAWING** Dimensions  
in mm



(Back side)



① T1 TERMINAL  
② T2 TERMINAL  
③ GATE TERMINAL

SOT-89

## APPLICATION

Hybrid IC, solid state relay,  
control of household equipment such as electric fan · washing machine,  
other general purpose control applications

## MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		8 (marked "B*")	
VDRM	Repetitive peak off-state voltage*1	400	V
VDSM	Non-repetitive peak off-state voltage*1	500	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, Ta=40°C*4	0.8	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	8	A
I <sup>2</sup> t	I <sup>2</sup> t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	0.26	A <sup>2</sup> s
PGM	Peak gate power dissipation		1	W
PG (AV)	Average gate power dissipation		0.1	W
VGM	Peak gate voltage		6	V
IGM	Peak gate current		1	A
Tj	Junction temperature		-40 ~ +125	°C
Tstg	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	48	mg

\*1. Gate open.

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## ELECTRICAL CHARACTERISTICS

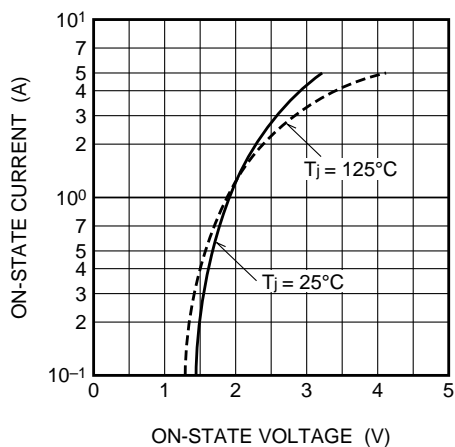
Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDRM	Repetitive peak off-state current	T <sub>j</sub> =125°C, V <sub>DRM</sub> applied	—	—	1.0	mA	
V <sub>TM</sub>	On-state voltage	T <sub>c</sub> =25°C, I <sub>TM</sub> =1.2A, Instantaneous measurement	—	—	2.0	V	
V <sub>FGT I</sub>	Gate trigger voltage *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	2.0	V
V <sub>RGT I</sub>			II	—	—	2.0	V
V <sub>RGT III</sub>			III	—	—	2.0	V
V <sub>FGT III</sub>			IV	—	—	2.0	V
I <sub>FGT I</sub>	Gate trigger current *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	5	mA
I <sub>RGT I</sub>			II	—	—	5	mA
I <sub>RGT III</sub>			III	—	—	5	mA
I <sub>FGT III</sub>			IV	—	—	10	mA
V <sub>GD</sub>	Gate non-trigger voltage	T <sub>j</sub> =125°C, V <sub>D</sub> =1/2V <sub>DRM</sub>	0.1	—	—	V	
R <sub>th(j-a)</sub>	Thermal resistance	Junction to case *4	—	—	65	°C/W	
(dv/dt) <sub>c</sub>	Critical-rate of rise of off-state commutating voltage		*3	—	—	V/μs	

\*2. Measurement using the gate trigger characteristics measurement circuit.  
 \*3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.  
 \*4. Mounted on 25mm × 25mm × 0.7mm ceramic plate with solder.

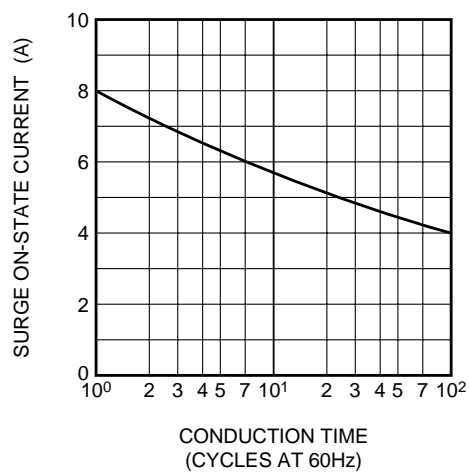
Voltage class	V <sub>DRM</sub> (V)	(dv/dt) <sub>c</sub>		Test conditions	Commutating voltage and current waveforms (inductive load)
		Min.	Unit		
8	400	2	V/μs	1. Junction temperature T <sub>j</sub> =125°C 2. Rate of decay of on-state commutating current (di/dt) <sub>c</sub> =-0.4A/ms 3. Peak off-state voltage V <sub>D</sub> =400V	

## PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTICS

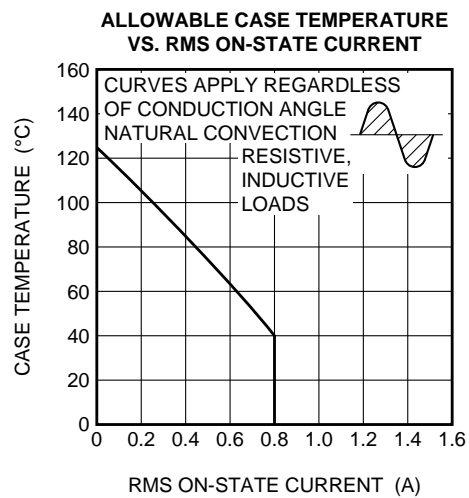
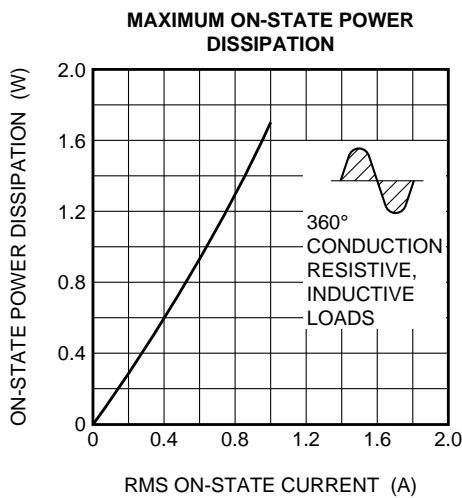
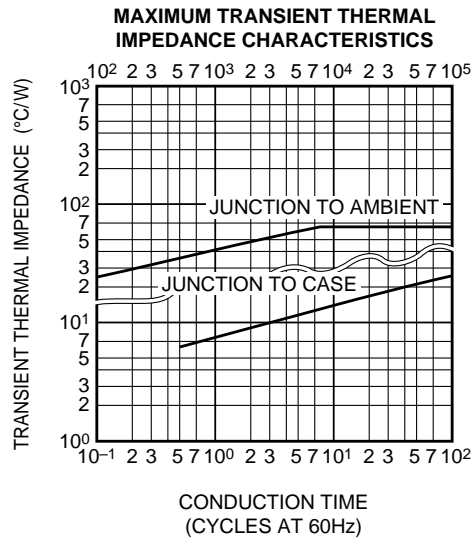
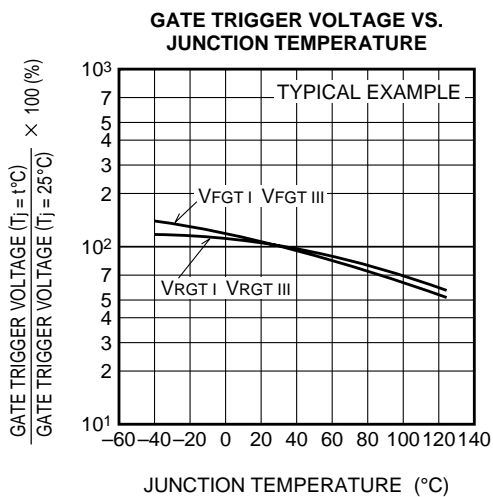
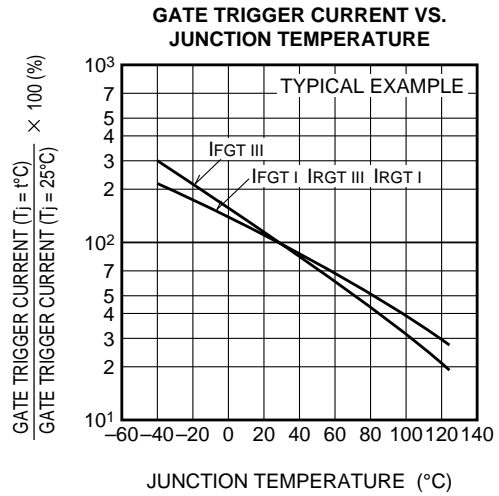
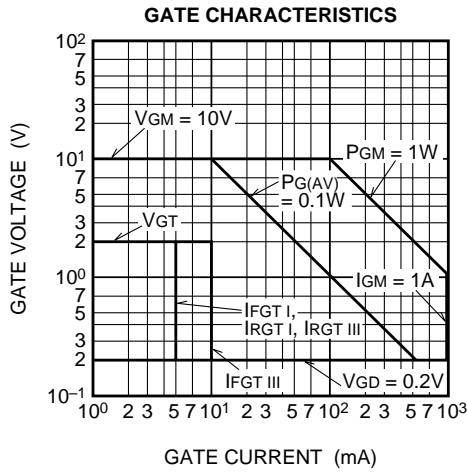


RATED SURGE ON-STATE CURRENT



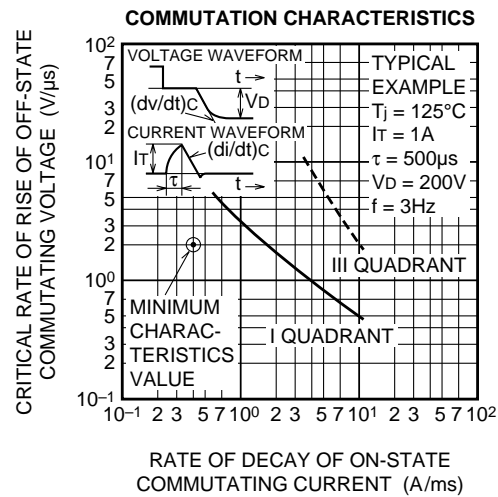
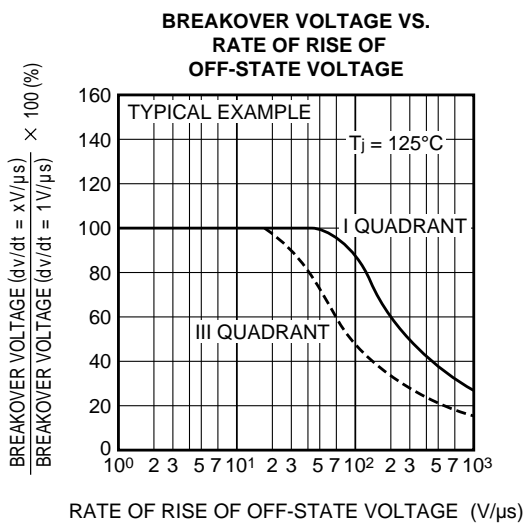
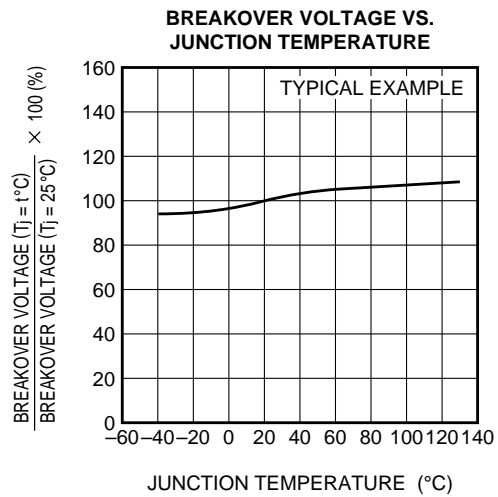
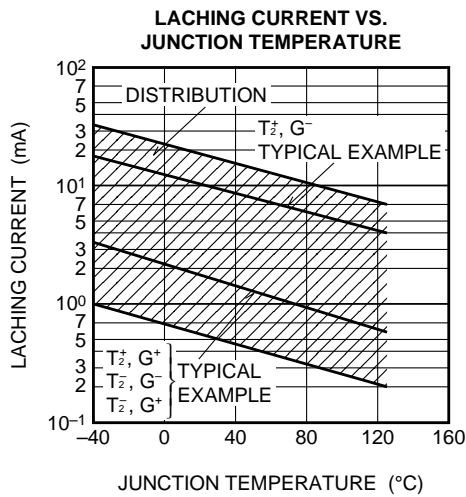
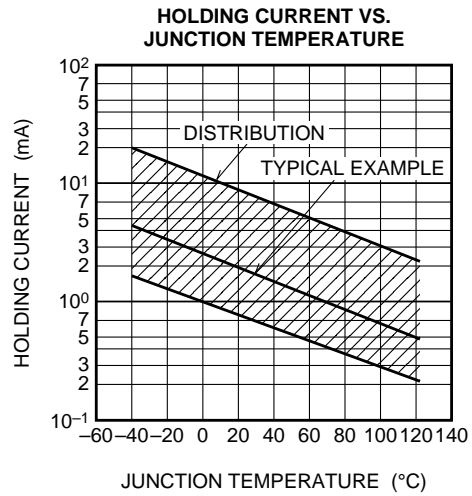
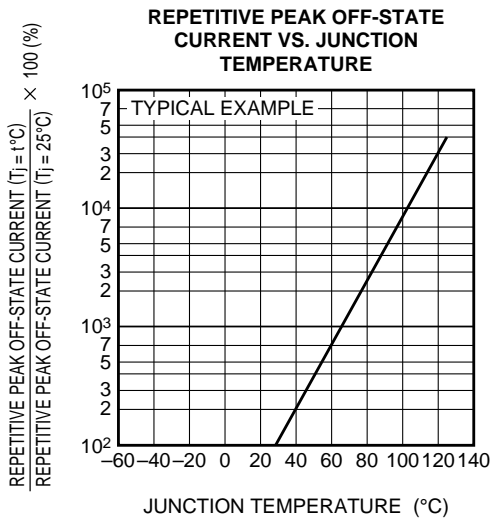
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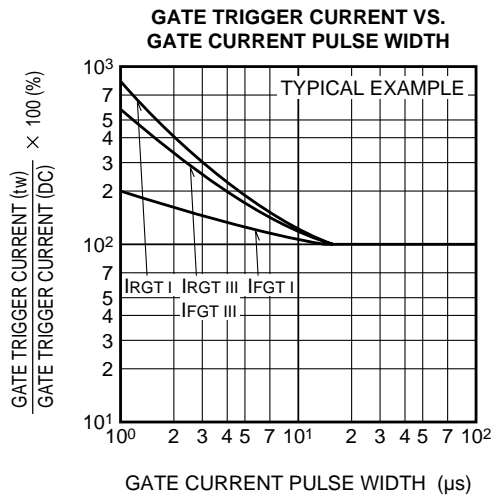
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**GATE TRIGGER CHARACTERISTICS  
TEST CIRCUITS**

